

Tadatomo T Suga

List of Publications by Year in descending order

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546
papers

7,973
citations

57758

44
h-index

88630

70
g-index

551
all docs

551
docs citations

551
times ranked

3288
citing authors

#	ARTICLE	IF	CITATIONS
1	Hydrophilic nanoporous copper surface prepared by modified formic acid vapor treatment. <i>Surfaces and Interfaces</i> , 2022, 28, 101620.	3.0	2
2	Low-temperature bonding of surface-activated polyimide to Cu Foil in Pt-catalyzed formic acid atmosphere. <i>Journal of Materials Science: Materials in Electronics</i> , 2022, 33, 2582-2589.	2.2	3
3	A novel strategy for GaN-on-diamond device with a high thermal boundary conductance. <i>Journal of Alloys and Compounds</i> , 2022, 905, 164076.	5.5	11
4	Quantification of wafer bond strength under controlled atmospheres. <i>Japanese Journal of Applied Physics</i> , 2022, 61, SF1010.	1.5	9
5	Thermodynamics of Ion-Cutting of $\text{I}^2\text{-Ga}_{2\text{O}_3}$ and Wafer-Scale Heterogeneous Integration of a $\text{I}^2\text{-Ga}_{2\text{O}_3}$ Thin Film onto a Highly Thermal Conductive SiC Substrate. <i>ACS Applied Electronic Materials</i> , 2022, 4, 494-502.	4.3	12
6	Polishing Diamond Substrates using Gas Cluster Ion Beam (GCIB) Irradiation for the Direct Bonding to Power Devices. , 2022, , .		0
7	Prolongation of the Surface Activation Effect using Self-Assembled Monolayer for Low Temperature Bonding of Au. , 2022, , .		1
8	Exploration of the enhanced performances for silk fibroin/sodium alginate composite coatings on biodegradable $\text{Mg}^{\sim}\text{Zn}^{\sim}\text{Ca}$ alloy. <i>Journal of Magnesium and Alloys</i> , 2021, 9, 1578-1594.	11.9	29
9	Heterogeneous GaN-Si integration via plasma activation direct bonding. <i>Journal of Alloys and Compounds</i> , 2021, 852, 156933.	5.5	10
10	Room Temperature Wafer Bonding of Glass Using Aluminum Oxide Intermediate Layer. <i>Advanced Materials Interfaces</i> , 2021, 8, 2001741.	3.7	14
11	Transfer of Ferroelectric Thin Film Capacitor Using Internal Stress of Plated Film. <i>IEEJ Transactions on Sensors and Micromachines</i> , 2021, 141, 39-43.	0.1	0
12	Channel Properties of $\text{Ga}_{\sim}\text{O}_{\sim}\text{f-on-SiC}$ MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 1185-1189.	3.0	17
13	Evidence for intermolecular forces involved in ladybird beetle tarsal setae adhesion. <i>Scientific Reports</i> , 2021, 11, 7729.	3.3	8
14	A Novel Preparation of Ag Agglomerates Paste with Unique Sintering Behavior at Low Temperature. <i>Micromachines</i> , 2021, 12, 521.	2.9	4
15	Sequential Plasma Activation for Low Temperature Bonding of Aluminosilicate Glass. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 054007.	1.8	9
16	Enhancement and Mechanism of Copper Nanoparticle Sintering in Activated Formic Acid Atmosphere at Low Temperature. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 054004.	1.8	9
17	Effect of Sequential Plasma Activation on Al_2O_3 for Low Temperature Bonding of Glass. , 2021, , .		0
18	Surface Activated Bonding of Glass Wafers using Oxide Intermediate Layer. , 2021, , .		3

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19	Thermal Visualization of Buried Interfaces Enabled by Ratio Signal and Steady-State Heating of Time-Domain Thermoreflectance. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 31843-31851.	8.0	19
20	Silicate glass-to-glass hermetic bonding for encapsulation of next-generation optoelectronics: A review. <i>Materials Today</i> , 2021, 47, 131-155.	14.2	18
21	Demonstration of high thermal performance GaN-on-graphite composite bonded substrate for application in III-V nitride electronics. <i>Applied Physics Express</i> , 2021, 14, 091002.	2.4	3
22	Fabrication of Ag@Ag ₂ O-MnOx composite nanowires for high-efficient room-temperature removal of formaldehyde. <i>Journal of Materials Science and Technology</i> , 2021, 91, 5-16.	10.7	16
23	Enhancement of Copper Nanoparticle Paste by Pressure-less Sintering on Different Substrates in Pt-catalyzed Formic Acid Atmosphere. , 2021, , .		0
24	Direct Cu to Cu Bonding and Alternative Bonding Techniques in 3D Packaging. <i>Springer Series in Advanced Microelectronics</i> , 2021, , 201-231.	0.3	4
25	Efficient thermal dissipation in wafer-scale heterogeneous integration of single-crystalline $\text{In}_2\text{Ga}_2\text{O}_3$ thin film on SiC. <i>Fundamental Research</i> , 2021, 1, 691-696.	3.3	20
26	Quantification of Wafer Bond Strength of Silicon Nitride under Controlled Atmosphere. , 2021, , .		0
27	Direct bonding of high dielectric oxides for high-performance transistor applications. <i>Scripta Materialia</i> , 2020, 178, 307-312.	5.2	18
28	Formation of smooth Au surfaces produced by multiple thin-film transfer process based on template stripping for low-temperature bonding. , 2020, , .		2
29	Direct Bonding of GaN to Diamond Substrate at Room Temperature. , 2020, , .		4
30	Thermal Transport across Ion-Cut Monocrystalline $\text{In}_2\text{Ga}_2\text{O}_3$ Thin Films and Bonded $\text{In}_2\text{Ga}_2\text{O}_3/\text{SiC}$ Interfaces. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 44943-44951.	8.0	66
31	Effect of Au Film Thickness and Surface Roughness on Room-Temperature Wafer Bonding and Wafer-Scale Vacuum Sealing by Au-Au Surface Activated Bonding. <i>Micromachines</i> , 2020, 11, 454.	2.9	23
32	Rapid pressureless and low-temperature bonding of large-area power chips by sintering two-step activated Ag paste. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 6497-6505.	2.2	12
33	Room-temperature pressureless wafer-scale hermetic sealing in air and vacuum using surface activated bonding with ultrathin Au films. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SBBB01.	1.5	7
34	Robust Ag-Cu Sintering Bonding at 160 $^{\circ}\text{C}$ via Combining Ag ₂ O Microparticle Paste and Pt-Catalyzed Formic Acid Vapor. <i>Metals</i> , 2020, 10, 315.	2.3	11
35	Recycled low-temperature direct bonding of Si/glass and glass/glass chips for detachable micro/nanofluidic devices. <i>Journal of Materials Science and Technology</i> , 2020, 46, 156-167.	10.7	21
36	Enhanced adhesion and anticorrosion of silk fibroin coated biodegradable Mg-Zn-Ca alloy via a two-step plasma activation. <i>Corrosion Science</i> , 2020, 168, 108466.	6.6	36

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37	Interfacial Thermal Conductance across Room-Temperature-Bonded GaN/Diamond Interfaces for GaN-on-Diamond Devices. ACS Applied Materials & Interfaces, 2020, 12, 8376-8384.	8.0	109
38	\hat{I}^2 -Ga ₂ O ₃ MOSFETs on the Si substrate fabricated by the ion-cutting process. Science China: Physics, Mechanics and Astronomy, 2020, 63, 1.	5.1	34
39	Emerging wafer bonding technologies. , 2020, , 627-639.		0
40	High Thermal Boundary Conductance across Bonded Heterogeneous GaN-SiC Interfaces. ACS Applied Materials & Interfaces, 2019, 11, 33428-33434.	8.0	82
41	GaN-SiC and GaN-diamond integration via room temperature bonding. , 2019, , .		0
42	Nano-Cu paste sintering in Pt-catalyzed formic acid vapor for Cu bonding at a low temperature. , 2019, , .		2
43	Room-Temperature Wafer Bonding with Titanium Thin Films Based on Formation of Ti/Si Amorphous Layers. , 2019, , .		0
44	Room Temperature Bonding of Quartz Glass using Aluminum Oxide Intermediate Layer. , 2019, , .		1
45	Low temperature Cu bonding with large tolerance of surface oxidation. AIP Advances, 2019, 9, .	1.3	9
46	Temporary SiC-SiC Wafer Bonding Compatible with High Temperature Annealing. , 2019, , .		0
47	SiC-SiC temporary bonding compatible with rapid thermal annealing at 1000 Å°C. , 2019, , .		0
48	Wafer-scale Au-Au surface activated bonding using atmospheric-pressure plasma. , 2019, , .		2
49	Room temperature SiC wafer bonding using SAB methods. , 2019, , .		0
50	Room-temperature pressureless wafer sealing using ultrathin Au films activated by Ar plasma. , 2019, , .		1
51	Integration of GaN-SiC and GaN-diamond by surface activated bonding methods. , 2019, , .		0
52	Wafer Bonding of SiC-AlN at Room Temperature for All-SiC Capacitive Pressure Sensor. Micromachines, 2019, 10, 635.	2.9	4
53	Moiré-Based Alignment Using Centrosymmetric Grating Marks for High-Precision Wafer Bonding. Micromachines, 2019, 10, 339.	2.9	6
54	Comparison of Argon and Oxygen Plasma Treatments for Ambient Room-Temperature Wafer-Scale Au-Au Bonding Using Ultrathin Au Films. Micromachines, 2019, 10, 119.	2.9	42

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55	Room-temperature bonding of organic films using ultrathin Au intermediate layers for organic integrated optical devices. , 2019, , .		1
56	Low Temperature Copper-Copper Bonding in Ambient Air Using Hydrogen Radical Pretreatment. , 2019, , .		0
57	First Demonstration of Waferscale Heterogeneous Integration of Ga ₂ O ₃ MOSFETs on SiC and Si Substrates by Ion-Cutting Process. , 2019, , .		42
58	The integration of Ga ₂ O ₃ on SiC at room temperature by surface activated bonding method. , 2019, , .		0
59	Low temperature all-Cu bonding via Cu-nanoparticle paste sintering in Pt-catalyzed formic acid vapor. , 2019, , .		0
60	Microsystem Integration and Packaging – A Chronicle of the Surface Activated Bonding and its Future Outlook. , 2019, , .		0
61	De-bondable SiC SiC wafer bonding via an intermediate Ni nano-film. Applied Surface Science, 2019, 465, 591-595.	6.1	12
62	Direct wafer bonding of Ga ₂ O ₃ –SiC at room temperature. Ceramics International, 2019, 45, 6552-6555.	4.8	40
63	Growth Behavior of Au Films on SiO ₂ Film and Direct Transfer for Smoothing Au Surfaces. International Journal of Automation Technology, 2019, 13, 254-260.	1.0	3
64	X-ray Photoelectron Spectroscopy (XPS) Analysis of Oxidation Behavior of Hydrogen-radical-treated Cu Surfaces. IEEJ Transactions on Sensors and Micromachines, 2019, 139, 38-39.	0.1	0
65	Investigation of Plasma Treatment Conditions for Wafer-Scale Room-Temperature Bonding Using Ultrathin Au Films in Ambient Air. IEEJ Transactions on Sensors and Micromachines, 2019, 139, 217-218.	0.1	0
66	Room temperature bonding and debonding of polyimide film and glass substrate based on surface activate bonding method. Japanese Journal of Applied Physics, 2018, 57, 02BB05.	1.5	5
67	Low Temperature Bonding for 3D Integration. Japanese Journal of Applied Physics, 2018, 57, 02B001.	1.5	0
68	Graphene transfer by surface activated bonding with poly(methyl glutarimide). Japanese Journal of Applied Physics, 2018, 57, 02BB02.	1.5	1
69	Evaluation of hydrogen radical treatment for indium surface oxide removal and analysis of re-oxidation behavior. Japanese Journal of Applied Physics, 2018, 57, 02BC01.	1.5	4
70	Bonding and transferring of carbon nanotube bumps using magnetron sputtering. Japanese Journal of Applied Physics, 2018, 57, 02BC02.	1.5	0
71	Study of Cu Film Surface Treatment Using Formic Acid Vapor/Solution for Low Temperature Bonding. Journal of the Electrochemical Society, 2018, 165, H3080-H3084.	2.9	12
72	Direct Homo/Heterogeneous Bonding of Silicon and Glass Using Vacuum Ultraviolet Irradiation in Air. Journal of the Electrochemical Society, 2018, 165, H3093-H3098.	2.9	19

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73	Sequential plasma activation methods for hydrophilic direct bonding at sub-200 Å°C. Japanese Journal of Applied Physics, 2018, 57, 02BD03.	1.5	20
74	Mechanism of bonding and debonding using surface activated bonding method with Si intermediate layer. Japanese Journal of Applied Physics, 2018, 57, 04FC11.	1.5	9
75	Properties of various plasma surface treatments for low-temperature Au–Au bonding. Japanese Journal of Applied Physics, 2018, 57, 04FC12.	1.5	13
76	Room temperature GaN-diamond bonding for high-power GaN-on-diamond devices. Scripta Materialia, 2018, 150, 148-151.	5.2	84
77	Low-temperature wafer direct bonding of silicon and quartz glass by a two-step wet chemical surface cleaning. Japanese Journal of Applied Physics, 2018, 57, 02BD02.	1.5	14
78	Surface analysis of argon and oxygen plasma-treated gold for room temperature wafer scale gold-gold bonding. , 2018, , .		0
79	Surface Activated Bonding Method for Low Temperature Bonding. , 2018, , .		6
80	Strain Effect in Highly Doped n-Type 3C-SiC on Glass Substrate for Mechanical Sensors and Mobility Enhancement. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800288.	1.8	5
81	Direct wafer bonding of GaN-SiC for high power GaN-on-SiC devices. Materialia, 2018, 3, 12-14.	2.7	20
82	(Invited) Room Temperature Wafer Bonding of Wide Bandgap Semiconductors. ECS Transactions, 2018, 86, 3-21.	0.5	1
83	Room-Temperature Wafer Bonding Using Smooth Au Thin Films for Integrated Plasmonic Devices. , 2018, , .		0
84	Cu film surface reduction through formic acid vapor/solution for 3-D interconnection. , 2018, , .		0
85	Room temperature GaN bonding by surface activated bonding methods. , 2018, , .		3
86	Low temperature de-oxidation for copper surface by catalyzed formic acid vapor. Applied Surface Science, 2018, 456, 890-898.	6.1	15
87	Feasibility study of all-SiC pressure sensor fabrication without deep etching. , 2018, , .		0
88	Reduction reaction analysis of nanoparticle copper oxide for copper direct bonding using formic acid. Japanese Journal of Applied Physics, 2017, 56, 04CC01.	1.5	14
89	Room Temperature SiC-SiO ₂ Wafer Bonding Enhanced by Using an Intermediate Si Nano Layer. ECS Journal of Solid State Science and Technology, 2017, 6, P227-P230.	1.8	10
90	GaN-Si direct wafer bonding at room temperature for thin GaN device transfer after epitaxial lift off. Applied Surface Science, 2017, 416, 1007-1012.	6.1	29

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91	A Comparative Study: Void Formation in Silicon Wafer Direct Bonding by Oxygen Plasma Activation with and without Fluorine. ECS Journal of Solid State Science and Technology, 2017, 6, P7-P13.	1.8	25
92	Room temperature bonding and debonding of PI film and glass substrate based on SAB method. , 2017, , .		1
93	Room-temperature direct bonding of silicon and quartz glass wafers. Applied Physics Letters, 2017, 110, .	3.3	29
94	Investigation of Thermal Treatment Processes for Dissimilar Wafer Bonding. ECS Transactions, 2017, 77, 143-152.	0.5	1
95	The effect of surface activation process for the GaAs device properties. , 2017, , .		0
96	Canary devices for through-silicon vias a condition monitoring approach. , 2017, , .		0
97	Combined surface activated bonding using H-containing HCOOH vapor treatment for Cu/Adhesive hybrid bonding at below 200 Å°C. Applied Surface Science, 2017, 414, 163-170.	6.1	14
98	Ar+H<inf>2</inf> atmospheric-pressure plasma treatment for Au-Au bonding and influence of air exposure on surface contamination. , 2017, , .		1
99	Low temperature Cu"Cu bonding by transient liquid phase sintering of mixed Cu nanoparticles and Sn"Bi eutectic powders. Journal of Materials Science: Materials in Electronics, 2017, 28, 16433-16443.	2.2	17
100	Hydrogen radical treatment for indium surface oxide removal and re-oxidation behaviour. , 2017, , .		4
101	Surface activated bonding of Si wafers at liquid nitrogen temperature. , 2017, , .		0
102	Hydrogen radical treatment for surface oxide removal from copper. , 2017, , .		3
103	Influence of geometric pattern design and surface roughness on thermal performance of copper to copper bonding. , 2017, , .		0
104	Wafer bonding using smooth titanium thin films in air atmosphere. , 2017, , .		0
105	Single-Crystalline 3C-SiC anodically Bonded onto Glass: An Excellent Platform for High-Temperature Electronics and Bioapplications. ACS Applied Materials & Interfaces, 2017, 9, 27365-27371.	8.0	49
106	Room-temperature transfer bonding of lithium niobate thin film on micromachined silicon substrate with Au microbumps. Sensors and Actuators A: Physical, 2017, 264, 274-281.	4.1	16
107	Interface properties of surface activated bonded CNT bumps and Au substrate. , 2017, , .		0
108	2D material transfer using room temperature bonding. , 2017, , .		1

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109	Fabrication and evaluation of molding and bonding tools for Au micromirror formation. , 2017, , .		0
110	Room Temperature Bonding with Polymethylglutarimide Using the Surface Activated Bonding Method for a Layer Transfer Platform. ECS Journal of Solid State Science and Technology, 2017, 6, P512-P516.	1.8	7
111	Introduction to the innovative interface bonding technology. , 2017, , .		1
112	Room temperature SiC-SiC direct wafer bonding by SAB methods. , 2017, , .		0
113	Low-temperature direct bonding of silicon to quartz glass wafer via sequential wet chemical surface activation. , 2017, , .		0
114	Novel sequential plasma activation method for direct glass bonding. , 2017, , .		2
115	Mechanisms for Room-Temperature Fluorine Containing Plasma Activated Bonding. ECS Journal of Solid State Science and Technology, 2017, 6, P373-P378.	1.8	17
116	Low temperature, low pressure, fluxless and plateless Cu-Cu bonding by Cu nano particle transient liquid phase sintering. , 2017, , .		0
117	Hydrogen radical treatment of printed indium solder paste for bump formation. , 2017, , .		2
118	Cu/Adhesive Hybrid Bonding at 180 Å°C in H-Containing HCOOH Vapor Ambient for 2.5D/3D Integration. , 2017, , .		8
119	Room Temperature Temporary Bonding of Glass Substrates Based on SAB Method Using Si Intermediate Layer. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2017, 7, 1713-1720.	2.5	13
120	Preparation of pine-like Cu-Ni-P coating and its application in 3D integration. , 2017, , .		0
121	Cu/adhesive hybrid bonding through a Cu-first bonding approach by using H-containing HCOOH vapor surface treatment. , 2017, , .		3
122	Study of Cu-Cu low temperature direct bonding and contact resistance measurement on bonding interface. , 2017, , .		1
123	SiC wafer bonding using surface activation method for power device. , 2017, , .		0
124	Room-Temperature Bonding of Wafers with Smooth Au Thin Films in Ambient Air Using a Surface-Activated Bonding Method. IEICE Transactions on Electronics, 2017, E100.C, 156-160.	0.6	33
125	Direct Cu to Cu Bonding and Other Alternative Bonding Techniques in 3D Packaging. Springer Series in Advanced Microelectronics, 2017, , 129-155.	0.3	16
126	Surface Activated Bonding and Debonding of Polymer Films and Glasses Using Si Nano-Adhesion Layer. Hyomen Kagaku, 2017, 38, 67-71.	0.0	0

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127	Direct bonding and debonding of glass wafers for handling of ultra-thin glass sheets. , 2016, , .		2
128	Room temperature bonding of Polymethylglutarimide for layer transfer method. , 2016, , .		0
129	Large area direct transfer technique for graphene onto substrates using self-assembly monolayer. , 2016, , .		1
130	A novel surface humidity controlled bonder for low-temperature wafer bonding. , 2016, , .		1
131	Contact Behavior among Vertically Aligned Carbon Nanotube Bumps under Compression for Flexible Multilayer Substrates. ECS Journal of Solid State Science and Technology, 2016, 5, M83-M87.	1.8	1
132	Room-Temperature Wafer Bonding Using Al/Ti/Au Layers for Integrated Reflectors in the Ultraviolet Spectral Region. , 2016, , .		1
133	Al/Au multilayers with different diffusion barrier layers for application as wafer-bonded UV reflectors. , 2016, , .		0
134	A Study of Void Formation in Fluorine Containing Plasma Activated Wafer Bonding. ECS Transactions, 2016, 75, 153-161.	0.5	1
135	Combined surface activation bonding for Cu/SiO ₂ hybrid bonding for 3D integration. , 2016, , .		2
136	Room Temperature Bonding with Lift-Off Resist Using the Surface Activated Bonding Method for a Layer Transfer Platform. ECS Transactions, 2016, 75, 197-202.	0.5	1
137	Combined surface-activated bonding technique for low-temperature hydrophilic direct wafer bonding. Japanese Journal of Applied Physics, 2016, 55, 04EC02.	1.5	11
138	Admittance spectroscopy analysis on the interfacial defect levels in the surface-activated bonding of GaAs. , 2016, , .		0
139	Direct Wafer Bonding of SiC-SiC at Room Temperature by SAB Method. ECS Transactions, 2016, 75, 77-83.	0.5	3
140	A Scalable Clean Graphene Transfer Process Using Polymethylglutarimide as a Support Scaffold. Journal of the Electrochemical Society, 2016, 163, E159-E161.	2.9	19
141	Transient liquid-phase sintering using silver and tin powder mixture for die bonding. Japanese Journal of Applied Physics, 2016, 55, 04EC14.	1.5	25
142	Room Temperature Bonding and Debonding of Ultra-Thin Glass Substrates for Fabrication of LCD. , 2016, , .		3
143	A comparison study: Direct wafer bonding of SiC-SiC by standard surface-activated bonding and modified surface-activated bonding with Si-containing Ar ion beam. Applied Physics Express, 2016, 9, 081302.	2.4	30
144	Room-Temperature Gold-Gold Bonding Method Based on Argon and Hydrogen Gas Mixture Atmospheric-Pressure Plasma Treatment for Optoelectronic Device Integration. IEICE Transactions on Electronics, 2016, E99.C, 339-345.	0.6	22

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145	Direct Wafer Bonding of SiC-SiC by SAB for Monolithic Integration of SiC MEMS and Electronics. ECS Journal of Solid State Science and Technology, 2016, 5, P451-P456.	1.8	20
146	Combined Surface Activated Bonding Technique for Hydrophilic SiO ₂ -SiO ₂ and Cu-Cu Bonding. ECS Transactions, 2016, 75, 117-128.	0.5	9
147	Combined Surface Activated Bonding Technique for Low-Temperature Cu/Dielectric Hybrid Bonding. ECS Journal of Solid State Science and Technology, 2016, 5, P419-P424.	1.8	32
148	The study of Cu-Cu low temperature bonding using formic acid treatment with/without Pt catalyst. , 2016, , .		4
149	Room-temperature wafer bonding of SiCâ€‘Si by modified surface activated bonding with sputtered Si nanolayer. Japanese Journal of Applied Physics, 2016, 55, 04EC09.	1.5	19
150	Simultaneous molding and low-temperature bonding of Au microstructures for fabrication of micromirrors on non-silicon substrates. , 2016, , .		0
151	(Invited) Surface Activated Wafer Bonding; Principle and Current Status. ECS Transactions, 2016, 75, 3-8.	0.5	3
152	Surface Activation and Planarization with Gas Cluster Ion Beam for Wafer Bonding. ECS Transactions, 2016, 75, 9-13.	0.5	4
153	Modified Surface Activated Bonding Using Si Intermediate Layer for Bonding and Debonding of Glass Substrates. ECS Transactions, 2016, 75, 185-189.	0.5	4
154	Nanomechanical Analysis of Polydimethylglutarimide Based Lift Off Resist Used for Temporary Bonding and Film Transfers. ECS Transactions, 2016, 75, 191-196.	0.5	0
155	(Invited) Analysis of Defect Levels at GaAs/GaAs Surface-Activated Bonding Interface for Multi-Junction Solar Cells. ECS Transactions, 2016, 75, 33-38.	0.5	0
156	Communicationâ€”Fluorinated Plasma Treatments Using PTFE Substrates for Room-Temperature Silicon Wafer Direct Bonding. ECS Journal of Solid State Science and Technology, 2016, 5, P393-P395.	1.8	6
157	Room-temperature wafer bonding using smooth gold thin films for wafer-level MEMS packaging. , 2016, , .		1
158	Review of Lowâ€‘Temperature Bonding Technologies and Their Application in Optoelectronic Devices. Electronics and Communications in Japan, 2016, 99, 63-71.	0.5	24
159	A Review of Low-temperature Sealing Technologies using Metal Thin Films and Solders for Sensors and MEMS. IEEJ Transactions on Sensors and Micromachines, 2016, 136, 266-273.	0.1	3
160	The room temperature bonding method of Al ₂ O ₃ barrier layers deposited using Atomic Layer Deposition. , 2015, , .		0
161	Room-temperature bonding method for polymer substrate of flexible electronics by surface activation using nano-adhesion layers. Japanese Journal of Applied Physics, 2015, 54, 101602.	1.5	20
162	Direct transfer of graphene onto transparent substrates with self-assembly monolayer. , 2015, , .		0

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163	Combined Surface-Activated Bonding Technique for Low-Temperature Cu/SiO ₂ Hybrid Bonding. ECS Transactions, 2015, 69, 79-88.	0.5	3
164	The influence of surface wettability on the ladybird beetles attachment to solid surfaces. , 2015, , .		0
165	Room Temperature Bonding of Al ₂ O ₃ Layers by Atomic Layer Deposition on Polyimide Substrates. ECS Transactions, 2015, 69, 99-105.	0.5	6
166	Process parameters for formic acid treatment with Pt catalyst for Cu direct bonding. , 2015, , .		3
167	Nanobonding: A key technology for emerging applications in health and environmental sciences. Japanese Journal of Applied Physics, 2015, 54, 030201.	1.5	8
168	Advances in Low-Temperature Bonding Technologies for 3D Integration. Japanese Journal of Applied Physics, 2015, 54, 030200.	1.5	0
169	Room-temperature direct bonding of germanium wafers by surface-activated bonding method. Japanese Journal of Applied Physics, 2015, 54, 030213.	1.5	19
170	Room temperature direct bonding and debonding of polyimide film on glass wafer using Si intermediate layer. , 2015, , .		0
171	Influence of atmospheric-pressure plasma treatment on surface and electrical properties of photodiode chips. , 2015, , .		0
172	Low temperature Au-Au surface-activated bonding using nitrogen atmospheric-pressure plasma treatment for optical microsystems. , 2015, , .		3
173	Influence of air exposure time on bonding strength in Au-Au surface activated wafer bonding. , 2015, , .		3
174	Bonding of polymer and glass using nano-adhesion layer for flexible electronics. , 2015, , .		0
175	Direct bonding for dissimilar metals assisted by carboxylic acid vapor. Japanese Journal of Applied Physics, 2015, 54, 030217.	1.5	6
176	Silicon carbide wafer bonding by modified surface activated bonding method. Japanese Journal of Applied Physics, 2015, 54, 030214.	1.5	32
177	Novel hydrophilic SiO ₂ wafer bonding using combined surface-activated bonding technique. Japanese Journal of Applied Physics, 2015, 54, 030218.	1.5	9
178	Surface activated bonding of GaAs and SiC wafers at room temperature for improved heat dissipation in high-power semiconductor lasers. Japanese Journal of Applied Physics, 2015, 54, 030207.	1.5	39
179	Fabrication of carbon nanotube bump interconnects for flexible multilayer substrates. Japanese Journal of Applied Physics, 2015, 54, 030205.	1.5	2
180	Fast atom bombardment onto vertically aligned multi-walled carbon nanotube bumps to achieve low interconnect resistance with Au layer. Microelectronics Reliability, 2015, 55, 2560-2564.	1.7	5

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181	Effect of ion species for the surface activated bonding of GaAs wafers on the characteristics of the bonded interfaces. , 2015, , .		2
182	Combined surface activated bonding (SAB) approach for SiO ₂ direct wafer bonding in vacuum. , 2015, , .		2
183	Wafer bonding of SiC-SiC and SiC-Si by modified surface activated bonding method. , 2015, , .		0
184	Surface activated bonding between bulk single crystal diamond and bulk aluminum. Japanese Journal of Applied Physics, 2015, 54, 081301.	1.5	7
185	Room temperature direct bonding and debonding of polymer film on glass wafer for fabrication of flexible electronic devices. , 2015, , .		3
186	Room-Temperature Wafer Bonding for High-Heat Dissipation Structure in High-Power Semiconductor Devices. Journal of Japan Institute of Electronics Packaging, 2015, 18, 463-468.	0.1	0
187	Low Temperature Bonding for 3D Integration-Surface Activated Bonding (SAB). Hyomen Kagaku, 2014, 35, 262-266.	0.0	0
188	Low-temperature gold-gold bonding using argon and hydrogen gas mixture atmospheric-pressure plasma treatment for optical microsystems. , 2014, , .		1
189	Miniaturized polarization sensors integrated with wire-grid polarizers. , 2014, , .		4
190	Room temperature bonding method for polymer films by surface activated bonding method using Al intermediate layer. , 2014, , .		3
191	Surface activated Ge/GaAs wafer bonding for multi-junction solar cells. , 2014, , .		3
192	Formic acid treatment with Pt catalyst for Cu direct bonding at low temperature. , 2014, , .		3
193	Combined Surface-Activated Bonding (SAB) Technologies for New Approach to Low Temperature Wafer Bonding. ECS Transactions, 2014, 64, 83-93.	0.5	1
194	Plasma assisted bonding of copper and silver substrates. , 2014, , .		2
195	Effects of Ar plasma and Ar fast atom bombardment (FAB) treatments on Cu/polymer hybrid surface for wafer bonding. , 2014, , .		4
196	Effects of Ar fast atom beam and Ar plasma irradiations on the biocompatibility of polymeric materials. , 2014, , .		0
197	Direct bonding of SiC by the surface activated bonding method. , 2014, , .		3
198	Low-Temperature Solid-State Bonding Using Hydrogen Radical Treated Solder for Optoelectronic and MEMS Packaging. ECS Transactions, 2014, 64, 267-274.	0.5	11

#	ARTICLE	IF	CITATIONS
199	Contact Behavior among Vertical Aligned Carbon Nanotube Bumps under Compression for Flexible Multilayer Substrates. ECS Transactions, 2014, 64, 21-26.	0.5	1
200	Novel sealing technology for organic EL display and lighting by means of modified surface activated bonding method. , 2014, , .		3
201	Low-temperature GaAs/SiC wafer bonding with Au thin film for high-power semiconductor lasers. , 2014, , .		5
202	Carbon nanotube bump interconnect for flexible multilayer substrates. , 2014, , .		1
203	Low temperature bonding for 3D. , 2014, , .		1
204	SiC wafer bonding by modified surface activated bonding method. , 2014, , .		1
205	Formic acid treatment with Pt catalyst for Cu direct and hybrid bonding at low temperature. , 2014, , .		2
206	Directly bonded Ge/GaAs by surface activated bonding for high efficiency III–V multi-junction solar cells. , 2014, , .		0
207	Cu/dielectric hybrid bonding using surface-activated bonding (SAB) technologies for 3D integration. , 2014, , .		1
208	Room-temperature wafer bonding with smooth Au thin film in ambient air using Ar RF plasma activation. , 2014, , .		5
209	Surface activated bonding method applied in MEMS pressure sensor with TSV structures. , 2014, , .		0
210	Fabrication of miniaturized polarization sensors using flip-chip bonding with atmospheric-pressure plasma activation. , 2014, , .		0
211	Effect of Formic Acid Vapor <itali>In Situ</itali> Treatment Process on Cu Low-Temperature Bonding. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2014, 4, 951-956.	2.5	25
212	Development of combined surface activated bonding (SAB) method for hydrophilic wafer bonding. , 2014, , .		0
213	Review of Low-temperature Bonding Technologies and Their Application in Optoelectronic Devices. IEJ Transactions on Sensors and Micromachines, 2014, 134, 159-165.	0.1	6
214	Spalling Technology of PZT Thin Film Capacitor using Internal Stress. IEJ Transactions on Sensors and Micromachines, 2014, 134, 85-89.	0.1	0
215	Toward a New Era of The Japan Institute for Electronics Packaging. Journal of Japan Institute of Electronics Packaging, 2014, 17, P4-P4.	0.1	0
216	Direct bonding of PEN at room temperature by means of surface activated bonding method using nano-adhesion layer. , 2013, , .		8

#	ARTICLE	IF	CITATIONS
235	Low temperature bonding for 3D interconnects. , 2012, , .		2
236	Behaviors of flexible vertically aligned carbon nanotube bumps under compression. , 2012, , .		2
237	Low-temperature hermetic packaging for microsystems using Au–Au surface-activated bonding at atmospheric pressure. Journal of Micromechanics and Microengineering, 2012, 22, 055026.	2.6	42
238	Comparison of SAB methods for room temperature bonding of Si wafers. , 2012, , .		0
239	Electrical properties of flexible Vertically aligned Carbon Nanotube bumps under compression. , 2012, , .		1
240	UV/vapor-assisted hybrid bonding technology as a tool for future nanopackaging. , 2012, , .		1
241	Formic acid with Pt catalyst combined treatment process for Cu low temperature bonding. , 2012, , .		1
242	Surface activated bonding and transfer of Carbon Nanotube bumps to Au substrates. , 2012, , .		2
243	Solid-state bonding using metallic cone layer for interconnection. , 2012, , .		1
244	Low temperature Cu/Cu direct bonding using formic gas in-situ treatment. , 2012, , .		2
245	Water vapor containing plasma activation for room-temperature bonding. , 2012, , .		0
246	Low temperature bonding for 3D integration — A review of the surface activated bonding (SAB). , 2012, , .		4
247	Vapor-assisted hybrid bonding of inorganic/organic substrates for 3D hetero integration. , 2012, , .		0
248	Hybrid integration of LiNbO ₃ thin films on micromachined Si substrates using room-temperature transfer bonding. , 2012, , .		0
249	Room Temperature Bonding of Polymer to Glass Wafers using Surface Activated Bonding (SAB) Method. ECS Meeting Abstracts, 2012, , .	0.0	0
250	Vapor-Assisted Surface Activation Method for Homo- and Heterogeneous Bonding of Cu, SiO ₂ , and Polyimide at 150Å°C and Atmospheric Pressure. Journal of Electronic Materials, 2012, 41, 2274-2280.	2.2	25
251	Nanoadhesion layer for enhanced Si–Si and Si–SiN wafer bonding. Microelectronics Reliability, 2012, 52, 342-346.	1.7	24
252	Investigation of fluorine containing plasma activation for room-temperature bonding of Si-based materials. Microelectronics Reliability, 2012, 52, 347-351.	1.7	23

#	ARTICLE	IF	CITATIONS
253	Low-Temperature Bonding of GaN on Si Using a Nonalloyed Metal Ohmic Contact Layer for GaN-Based Heterogeneous Devices. IEEE Journal of Quantum Electronics, 2012, 48, 182-186.	1.9	13
254	Low-temperature direct bonding of glass nanofluidic chips using a two-step plasma surface activation process. Analytical and Bioanalytical Chemistry, 2012, 402, 1011-1018.	3.7	80
255	Recent Developments in Bonding Technology for Inorganic and Organic Materials. Journal of the Vacuum Society of Japan, 2012, 55, 487-492.	0.3	3
256	Theory and Experiment for Capillary Condensation of Water on Metal Oxide Films in a Humid Environment Studied by Atomic Force Microscope. IEJ Transactions on Sensors and Micromachines, 2012, 132, 397-406.	0.1	0
257	Homogenizing and Applying Dielectric Film to Wafer-Level Film Preparation. Transactions of the Japan Institute of Electronics Packaging, 2012, 5, 92-98.	0.4	2
258	Anti-Stiction Coatings for MEMS Switches Based on Quantitative Evaluation of Adhesion Forces. Journal of Japan Institute of Electronics Packaging, 2012, 15, 49-58.	0.1	0
259	Low-temperature Bonding Technologies and Their Application to Highly Functional Sensors. Journal of Smart Processing, 2012, 1, 106-113.	0.1	0
260	Long Life and Low Consumption System for Sustainable Development. , 2012, , 1040-1043.		0
261	Fabrication and Characterization of Ferroelectric PZT and BaTiO ₃ Thin Films on Releasable Electrode Structures. Transactions of the Japan Institute of Electronics Packaging, 2012, 5, 34-40.	0.4	1
262	Homo/heterogeneous bonding of Cu, SiO ₂ , and polyimide by low temperature vapor-assisted surface activation method. , 2011, , .		9
263	Nanoprecision aligned wafer direct bonding and its outlook. , 2011, , .		0
264	Surface activated bonding of copper through silicon vias and gold stud bumps at room temperature. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, 021007.	2.1	9
265	Formic acid vapor treated Cu-Cu direct bonding at low temperature. , 2011, , .		4
266	Low temperature Cu-Cu direct bonding using formic acid vapor pretreatment. , 2011, , .		20
267	Air-gap structure between integrated LiNbO ₃ optical modulators and micromachined Si substrates. Optics Express, 2011, 19, 15739.	3.4	34
268	Si nanoadhesion layer for enhanced SiO ₂ /SiN wafer bonding. Scripta Materialia, 2011, 65, 320-322.	5.2	46
269	Investigation of anti-stiction coating for ohmic contact MEMS switches with thiophenol and 2-naphthalenethiol self-assembled monolayer. Sensors and Actuators A: Physical, 2011, 172, 455-461.	4.1	11
270	Nanobonding Technology Toward Electronic, Fluidic, and Photonic Systems Integration. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 689-703.	2.9	37

#	ARTICLE	IF	CITATIONS
271	Passive Alignment and Mounting of LiNbO ₃ Waveguide Chips on Si Substrates by Low-Temperature Solid-State Bonding of Au. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 652-658.	2.9	37
272	Notice of Retraction Surface activated bonding as nano-packaging technology. , 2011, , .		0
273	Low-temperature sealing for optical microsystem packages using Au-Au surface activated bonding in atmospheric pressure environment. , 2011, , .		1
274	Room-Temperature Direct Bonding Using Fluorine Containing Plasma Activation. Journal of the Electrochemical Society, 2011, 158, H525.	2.9	26
275	Surface activation-based nanobonding and interconnection at room temperature. Journal of Micromechanics and Microengineering, 2011, 21, 025009.	2.6	10
276	Room temperature SiO ₂ /wafer bonding by adhesion layer method. , 2011, , .		22
277	An Electrode Structure for Ferroelectric Thin Films and Its Application to the Nanotransfer Method. Transactions of the Japan Institute of Electronics Packaging, 2011, 4, 40-43.	0.4	3
278	Final program ICSJ 2010. , 2010, , .		0
279	Investigation of bonding strength and sealing behavior of aluminum/stainless steel bonded at room temperature. Vacuum, 2010, 84, 1334-1340.	3.5	27
280	Comparative annealing effect on bonded wafers in air and ultrahigh vacuum for microelectromechanical systems/microfluidics packaging. Journal of Micro/ Nanolithography, MEMS, and MOEMS, 2010, 9, 041107.	0.9	4
281	Interfacial Behavior of Surface Activated p-GaP/n-GaAs Bonded Wafers at Room Temperature. Electrochemical and Solid-State Letters, 2010, 13, H61.	2.2	27
282	Evaluation of surface microroughness for surface activated bonding. , 2010, , .		9
283	Integrated micro laser Doppler velocimeter with 3-D structure. , 2010, , .		1
284	Metal surface cleanliness and its improvement on bonding. , 2010, , .		0
285	A novel room-temperature wafer direct bonding method by fluorine containing plasma activation. , 2010, , .		4
286	Room-temperature Si-Si and Si-SiN wafer bonding. , 2010, , .		15
287	Room-Temperature Bonding Using Fluorine Containing Plasma Activation and Its Bonding Mechanism. ECS Transactions, 2010, 33, 485-494.	0.5	1
288	Micromachined Silicon Disk Resonator Transduced by Piezoelectric Lead Zirconate Titanate Thin Films. Japanese Journal of Applied Physics, 2010, 49, 06GN17.	1.5	7

#	ARTICLE	IF	CITATIONS
289	Preparation of ferroelectric capacitor films onto the releasable substrate and its application to nano-transfer method. , 2010, , .		1
290	Influence of bonding atmosphere on low-temperature wafer bonding. , 2010, , .		1
291	Modified diffusion bonding for both Cu and SiO ₂ at 150 °C in ambient air. , 2010, , .		8
292	Room-temperature Si-SiN wafer bonding by nano-adhesion layer method. , 2010, , .		5
293	Novel room-temperature fluorine containing plasma activated bonding and its improvements. , 2010, , .		0
294	Characterization of surface profile for surface activated bonding by using Power Spectral Density function. , 2010, , .		0
295	Surface Activated Bonding between Au layer and vertically aligned Multi-Wall Carbon Nanotubes. , 2010, , .		2
296	Room-Temperature Bonding of GaN to Al Using Ar-Beam Surface Activation. IEEJ Transactions on Sensors and Micromachines, 2010, 130, 369-372.	0.1	0
297	Pressure Dependence of Resonant Characteristics of Lateral Comb Drive Resonators in the Free-Molecule Regime. Applied Physics Express, 2009, 2, 096501.	2.4	2
298	Residue-Free Solder Bumping Using Small AuSn Particles by Hydrogen Radicals. IEICE Transactions on Electronics, 2009, E92-C, 247-251.	0.6	6
299	Fine pitch and high density Sn bump fabrication. , 2009, , .		1
300	Heterogeneous integration towards an ultra-compact and thin optical displacement microsensors. , 2009, , .		0
301	Highly integrated ultra-sensitive silicon disk micro resonator for trace amount of chemicals detection. , 2009, , .		0
302	Low-temperature wafer bonding using gold layers. , 2009, , .		12
303	A novel moiré fringe assisted method for nanoprecision alignment in wafer bonding. , 2009, , .		7
304	Surface activated bonding of 8 in. Si wafers for MEMS and microfluidic packaging. , 2009, , .		1
305	Low-temperature bonding of photodiodes on glass substrate using Au stud bumps and its application to microsensors with three-dimensional structure. , 2009, , .		0
306	High-Precision Alignment for Low Temperature Wafer Bonding. ECS Transactions, 2009, 16, 539-548.	0.5	1

#	ARTICLE	IF	CITATIONS
307	Modified diffusion bond process for chemical mechanical polishing (CMP)-Cu at 150°C in ambient air. , 2009, , .		7
308	Hybrid Bonding (Plasma activation and Anodic bonding) for Vacuum Sealing. ECS Transactions, 2009, 16, 517-524.	0.5	1
309	Role of Heating on Plasma-Activated Silicon Wafers Bonding. Journal of the Electrochemical Society, 2009, 156, H846.	2.9	25
310	Au—Au Surface-Activated Bonding and Its Application to Optical Microsensors With 3-D Structure. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1500-1505.	2.9	95
311	Moiré method for nanoprecision wafer-to-wafer alignment: Theory, simulation and application. , 2009, , .		11
312	Wetting behavior of electrolyte in fine pitch Cu/Sn bumping process by electroplating. , 2009, , .		1
313	Low-temperature bonding of laser diode chips on Si substrates with oxygen and hydrogen atmospheric-pressure plasma activation. , 2009, , .		7
314	Investigation of anti-stiction coating using π-conjugated hydrophobic self-assembled monolayer for ohmic contact MEMS switch. , 2009, , .		0
315	High-Precision Alignment for Low-Temperature Wafer Bonding. Journal of the Electrochemical Society, 2009, 156, H197.	2.9	6
316	Development of a new miniaturized 300-MHZ frequency band antenna for wireless microsensor nodes. , 2009, , .		0
317	Optical Microsensors Integration Technologies for Biomedical Applications. IEICE Transactions on Electronics, 2009, E92-C, 231-238.	0.6	13
318	Effects of Surface Profiles of As-Sputtered Au Thin Films on Room Temperature Seal-Bonding. Journal of Japan Institute of Electronics Packaging, 2009, 12, 534-541.	0.1	2
319	Development of the Dedicated Device for Characterization of Vacuum Sealing Using SCREAM Method. Journal of Japan Institute of Electronics Packaging, 2009, 12, 526-533.	0.1	0
320	P-MNS-07 NANOTRANSFER METHOD FOR THE FERROELECTRIC FILMS ONTO THE POLYMER SUBSTRATE(Micro/Nanosystem Science and Technology,Technical Program of Poster Session). Proceedings of JSME-IIP/ASME-ISPS Joint Conference on Micromechatronics for Information and Precision Equipment IIP/ISPS Joint MIPE, 2009, 2009, 429-430.	0.0	0
321	Wafer level sealing characterization method using Si micro cantilevers. Sensors and Actuators A: Physical, 2008, 147, 359-364.	4.1	13
322	The influence of surface profiles on leakage in room temperature seal-bonding. Sensors and Actuators A: Physical, 2008, 144, 124-129.	4.1	15
323	A digital output piezoelectric accelerometer for ultra-low power wireless sensor node. , 2008, , .		7
324	Room temperature wafer bonding using surface activated bonding method. , 2008, , .		8

#	ARTICLE	IF	CITATIONS
325	Three-dimensional integration of optical multi-chips using surface-activated bonding for high-density microsystems packaging. , 2008, , .		1
326	20- μ m-pitch Au micro-bump interconnection at room temperature in ambient air. , 2008, , .		12
327	Bumpless Interconnect of 6- μ m-Pitch Cu Electrodes at Room Temperature. IEEE Transactions on Advanced Packaging, 2008, 31, 473-478.	1.6	63
328	The chip-on-board bonding using non-conductive film and metallic bumps by the surface activated bonding method. , 2008, , .		0
329	Bumpless interconnect of 6- μ m pitch Cu electrodes at room temperature. , 2008, , .		8
330	Void-Free Room-Temperature Silicon Wafer Direct Bonding Using Sequential Plasma Activation. Japanese Journal of Applied Physics, 2008, 47, 2526.	1.5	30
331	Low-Temperature Bumpless Bonding for Surface Acoustic Wave Components. Japanese Journal of Applied Physics, 2008, 47, 2521-2525.	1.5	0
332	Effect of Surface Contamination on Solid-State Bondability of Sn-Ag-Cu Bumps in Ambient Air. Materials Transactions, 2008, 49, 1508-1512.	1.2	7
333	Low-Temperature Direct Bonding of Flip-Chip Mountable VCSELs with Au-Au Surface Activation. IEEE Transactions on Sensors and Micromachines, 2008, 128, 266-270.	0.1	17
334	Feasibility of SAB using Nano-adhesion Layer for Low Temperature GaN Wafer Bonding. , 2007, , .		1
335	Measurement of Alignment Accuracy for Wafer Bonding by Moiré Method. Japanese Journal of Applied Physics, 2007, 46, 1989-1993.	1.5	5
336	Room temperature GaN-GaAs direct bonding by argon-beam surface activation. Proceedings of SPIE, 2007, , .	0.8	4
337	Low-Temperature Process of Fine-Pitch Au-Sn Bump Bonding in Ambient Air. Japanese Journal of Applied Physics, 2007, 46, 1961-1967.	1.5	34
338	Microstructure Fabrication with Conductive Paste Dispensing. , 2007, , .		4
339	A Novel Bonding Method for Ionic Wafers. IEEE Transactions on Advanced Packaging, 2007, 30, 598-604.	1.6	36
340	Investigation of Anti-Stiction Coating for MEMS Switch using Atomic Force Microscope. , 2007, , .		3
341	Room Temperature Si/Si Wafer Direct Bonding in Air. , 2007, , .		4
342	Fritting Contact Using SnAu probe. , 2007, , .		0

#	ARTICLE	IF	CITATIONS
343	Effect of SAB process on GaN surfaces for low temperature bonding. , 2007, , .		3
344	Silicon Wafer Bonding by Modified Surface Activated Bonding Methods. , 2007, , .		0
345	Surface Activated Bonding Method for Flexible Lamination. , 2007, , .		1
346	Feasibility of Solid State Bonding for Sn-Ag-Cu Solder Bumps in Ambient Air. , 2007, , .		0
347	Development of high quality Pt-CeO ₂ composite anode for direct methanol fuel cell applications. , 2007, , .		0
348	The Influence of surface Profile on Leakage in Roomtemperature Seal-Bonding. , 2007, , .		0
349	Finite Element Analysis of the Effect of Surface Roughness on Nanometer-scale Contact. , 2007, , .		3
350	Low-Force Electric Contact Processes on Cu Electrodes. IEEE Transactions on Electronics Packaging Manufacturing, 2007, 30, 194-199.	1.4	0
351	Low-Temperature Bonding of Laser Diode Chips on Silicon Substrates Using Plasma Activation of Au Films. IEEE Photonics Technology Letters, 2007, 19, 1994-1996.	2.5	108
352	Integration and Packaging Technologies for Small Biomedical Sensors. Journal of the Japan Society for Precision Engineering, 2007, 73, 1190-1194.	0.1	0
353	Low-cycle fatigue properties of eutectic solders at high temperatures. Fatigue and Fracture of Engineering Materials and Structures, 2007, 30, 413-419.	3.4	20
354	Low-Temperature Au-to-Au Bonding for LiNbO ₃ /Si Structure Achieved in Ambient Air. IEICE Transactions on Electronics, 2007, E90-C, 145-146.	0.6	19
355	UHV-Bonding and Reversible Interconnection. Transactions of the Japan Society for Aeronautical and Space Sciences, 2007, 49, 197-202.	0.7	4
356	3D Integration and Cu Direct Bonding. Journal of Japan Institute of Electronics Packaging, 2007, 10, 408-414.	0.1	0
357	Structural investigation of heat-treated fullerene nanotubes and nanowhiskers. Diamond and Related Materials, 2006, 15, 1143-1146.	3.9	27
358	Low temperature direct bonding of flip-chip mounting VCSEL to Si substrate. , 2006, , .		0
359	Cu-Cu Room Temperature Bonding - Current Status of Surface Activated Bonding(SAB) - ECS Transactions, 2006, 3, 155-163.	0.5	22
360	Bumpless Interconnect Through Ultrafine Cu Electrodes by Means of Surface-Activated Bonding (SAB) Method. IEEE Transactions on Advanced Packaging, 2006, 29, 218-226.	1.6	111

#	ARTICLE	IF	CITATIONS
361	Mechanism of ultra low force probing on Al electrodes. , 2006, , .		0
362	Room/Low Temperature Interconnection Technique on Micro-bump/Film for COC and COF System. , 2006, , .		2
363	Room-Temperature Microfluidics Packaging Using Sequential Plasma Activation Process. IEEE Transactions on Advanced Packaging, 2006, 29, 448-456.	1.6	61
364	Development of wafer-scale sealing test using different size of micro-resonators. , 2006, , .		0
365	Surface-Activated Bonding of Aluminum/Stainless Steel and Its Seal Characteristics. Journal of the Japan Society for Technology of Plasticity, 2006, 47, 596-600.	0.3	0
366	Room temperature wafer level glass/glass bonding. Sensors and Actuators A: Physical, 2006, 127, 31-36.	4.1	70
367	Structure and electrical properties of heat-treated fullerene nanowhiskers as potential energy device materials. Journal of the European Ceramic Society, 2006, 26, 429-434.	5.7	30
368	Bumpless interconnect of ultrafine Cu electrodes by surface activated bonding (SAB) method. Electronics and Communications in Japan, 2006, 89, 34-42.	0.2	9
369	Low-temperature bonding of a LiNbO ₃ waveguide chip to a Si substrate in ambient air for hybrid-integrated optical devices. , 2006, 6376, 16.		3
370	Sequential Activation Process of oxygen RIE and nitrogen Radical for LiTaO ₃ and Si Wafer Bonding. ECS Transactions, 2006, 3, 91-98.	0.5	2
371	Room temperature bonding of silicon and lithium niobate. Applied Physics Letters, 2006, 89, 031914.	3.3	53
372	Sequential Plasma Activated Process for Silicon Direct Bonding. ECS Transactions, 2006, 3, 191-202.	0.5	24
373	Effect of Exposure to Vacuum Condition in Room-Temperature Direct Bonding of CMP-Cu Thin Films by Surface Activated Bonding (SAB) Method. Journal of Japan Institute of Electronics Packaging, 2006, 9, 278-281.	0.1	1
374	Study on Sn–Ag Oxidation and Feasibility of Room Temperature Bonding of Sn–Ag–Cu Solder. Materials Transactions, 2005, 46, 2431-2436.	1.2	27
375	Isothermal Fatigue Properties of Sn–Ag–Cu Alloy Evaluated by Micro Size Specimen. Materials Transactions, 2005, 46, 2309-2315.	1.2	46
376	Broadband MEMS shunt switches using PZT/HfO ₂ multi-layered high k dielectrics for high switching isolation. Sensors and Actuators A: Physical, 2005, 121, 275-281.	4.1	20
377	Electroplated Ni microcantilever probe with electrostatic actuation. Sensors and Actuators A: Physical, 2005, 123-124, 490-496.	4.1	10
378	Morphology of C ₆₀ nanotubes fabricated by the liquid"liquid interfacial precipitation method. Science and Technology of Advanced Materials, 2005, 6, 272-277.	6.1	56

#	ARTICLE	IF	CITATIONS
379	Characterization of fullerene nanotubes prepared by the liquid-liquid interfacial precipitation method. Science and Technology of Advanced Materials, 2005, 6, 388-393.	6.1	12
380	Direct bonding of CMP-Cu films by surface activated bonding (SAB) method. Journal of Materials Science, 2005, 40, 3149-3154.	3.7	78
381	Surface activated bonding of LCP/Cu for electronic packaging. Journal of Materials Science, 2005, 40, 3177-3184.	3.7	29
382	Surface Activated Flip-Chip Bonding of Laser Chips. , 2005, , 793.		0
383	<title>Mechanical properties of lead-free solder alloys evaluated by miniature size specimen</title>. , 2005, 5852, 297.		11
384	Necessary load for room temperature vacuum sealing. Journal of Micromechanics and Microengineering, 2005, 15, S281-S285.	2.6	17
385	Enhanced Cu/LCP adhesion by pre-sputter cleaning prior to Cu deposition. IEEE Transactions on Advanced Packaging, 2005, 28, 495-502.	1.6	19
386	Characterization of high-pressure sintered C60 nanowhiskers and C60 powder. Journal of Materials Research, 2005, 20, 742-746.	2.6	7
387	Low Cycle Fatigue Properties of Solder Alloys Evaluated by Micro Bulk Specimen. , 2005, , 1827.		5
388	Low temperature bonding of LiNbO 3 waveguide chips to Si substrates in air. , 2005, 6050, 288.		0
389	Low temperature bonded Cu/LCP materials for FPCs and their characteristics. IEEE Transactions on Components and Packaging Technologies, 2005, 28, 760-764.	1.3	14
390	Low-temperature LD direct bonding for highly functional optical MEMS. , 2005, , .		5
391	Low-temperature direct flip-chip bonding for integrated micro-systems. , 2005, , .		1
392	Structural characterization of the fullerene nanotubes prepared by the liquid-liquid interfacial precipitation method. Journal of Materials Research, 2005, 20, 688-695.	2.6	85
393	Structure and properties of fullerene nanowhiskers prepared by the liquid-liquid interfacial precipitation method. , 2004, 5648, 224.		5
394	Transmission electron microscopy investigation of fullerene nanowhiskers and needle-like precipitates formed by using C60 and (i-2-C60)Pt(PPh3)2. Journal of Materials Research, 2004, 19, 2410-2414.	2.6	25
395	Transmission electron microscopy investigation of tubular and capsular needlelike crystals of C60 produced by the liquid-liquid interfacial precipitation method. Journal of Materials Research, 2004, 19, 3145-3148.	2.6	20
396	Wafer Level Surface Activated Bonding Tool for MEMS Packaging. Journal of the Electrochemical Society, 2004, 151, G461.	2.9	67

#	ARTICLE	IF	CITATIONS
397	C3F8 plasma fluorination of lead free solders for fluxless soldering. Applied Surface Science, 2004, 227, 81-86.	6.1	15
398	Light emission during negative heavy ion implantation into lithium niobate and sapphire. Vacuum, 2004, 74, 367-371.	3.5	7
399	Hybrid integration technologies for optical micro-systems. , 2004, 5604, 67.		0
400	Nanoparticles formation in insulators induced by Au ⁺ and Au ²⁺ ion implantation. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 606-609.	1.4	8
401	Radiation effects in diamond induced by negative gold ions. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 947-951.	1.4	3
402	Reliability of Au bump ⁺ â€“Cu direct interconnections fabricated by means of surface activated bonding method. Microelectronics Reliability, 2003, 43, 751-756.	1.7	24
403	Electroplating Ni micro-cantilevers for low contact-force IC probing. Sensors and Actuators A: Physical, 2003, 103, 116-121.	4.1	52
404	Wafer-scale spontaneous bonding of silicon wafers by argon-beam surface activation at room temperature. Sensors and Actuators A: Physical, 2003, 105, 98-102.	4.1	80
405	New Au-Al interconnect technology and its reliability by surface activated bonding. , 2003, , .		1
406	Characterization of fritting phenomena on Al electrode for low contact force probe card. IEEE Transactions on Components and Packaging Technologies, 2003, 26, 382-387.	1.3	18
407	Room temperature Cu ⁺ â€“Cu direct bonding using surface activated bonding method. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2003, 21, 449-453.	2.1	268
408	Structural characterization of the C ₆₀ [C(COOC ₂ H ₅) ₂] whiskers prepared by the liquid ⁺ â€“liquid interfacial precipitation method. Journal of Materials Research, 2003, 18, 2730-2735.	2.6	36
409	Structural investigation of the C ₆₀ /C ₇₀ whiskers fabricated by forming liquid ⁺ â€“liquid interfaces of toluene with dissolved C ₆₀ /C ₇₀ and isopropyl alcohol. Journal of Materials Research, 2003, 18, 1096-1103.	2.6	68
410	Characterizing high-pressure compressed C ₆₀ whiskers and C ₆₀ powder. Journal of Materials Research, 2003, 18, 166-172.	2.6	6
411	Evaluation of Environmental Burden of Lead-Free Solders ⁺ â€“A Case of Sn-Zn Solder. Journal of Japan Institute of Electronics Packaging, 2003, 6, 375-379.	0.1	0
412	The Influence of the Heat after Bonding on the Separability at Gold Wire Bonding Area.. Journal of Japan Institute of Electronics Packaging, 2003, 6, 68-72.	0.1	0
413	Technological Tendency of Bonding for MEMS Device by Japanese Patent Research. Journal of Japan Institute of Electronics Packaging, 2003, 6, 602-609.	0.1	0
414	Resonant-typed microscanners fabricated by hybrid PZT deposition process on SOI wafers. , 2002, 4936, 215.		5

#	ARTICLE	IF	CITATIONS
415	Room-Temperature Wafer Bonding of Silicon and Lithium Niobate by Means of Argon-Beam Surface Activation. <i>Integrated Ferroelectrics</i> , 2002, 50, 53-59.	0.7	3
416	A new bumping process using lead-free solder paste. <i>IEEE Transactions on Electronics Packaging Manufacturing</i> , 2002, 25, 253-256.	1.4	9
417	Characterization of the bonding strength and interface current of p-Si/n-InP wafers bonded by surface activated bonding method at room temperature. <i>Journal of Applied Physics</i> , 2002, 91, 3062-3066.	2.5	48
418	The effect of prebonding heat treatment on the separability of Au wire from Ag-plated Cu alloy substrate. <i>IEEE Transactions on Electronics Packaging Manufacturing</i> , 2002, 25, 5-12.	1.4	1
419	Characteristics of low force contact process for MEMS probe cards. <i>Sensors and Actuators A: Physical</i> , 2002, 97-98, 462-467.	4.1	26
420	Development of Mems IC Probe Card Utilizing Fritting Contact. , 2002, , 314-318.		0
421	Room-temperature wafer bonding of Si to LiNbO ₃ , LiTaO ₃ and Gd ₃ Ga ₅ O ₁₂ by Ar-beam surface activation. <i>Journal of Micromechanics and Microengineering</i> , 2001, 11, 348-352.	2.6	77
422	Influence of ceramic surface treatment on peel-off strength between aluminum nitride and epoxy-modified polyaminobismaleimide adhesive. <i>IEEE Transactions on Advanced Packaging</i> , 2001, 24, 104-112.	1.6	22
423	Microsensors and actuator arrays based on Pb(Zr,Ti)O ₃ thin film for AFM data storage. , 2001, , .		7
424	Investigation of the bonding strength and interface current of p-Si/n-GaAs wafers bonded by surface activated bonding at room temperature. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 2114.	1.6	49
425	Characteristics of Low Force Contact Process for MEMS Probe Cards. , 2001, , 1394-1397.		3
426	Separable Wire Bonding and Application to the Interposer-Less CSP.. <i>Journal of Japan Institute of Electronics Packaging</i> , 2001, 4, 207-212.	0.1	0
427	An 8-inch Wafer Bonding Apparatus with Ultra-High Alignment Accuracy Using Surface Activated Bonding (SAB) Concept. , 2001, , 222-225.		0
428	Title is missing!. <i>Journal of Japan Institute of Electronics Packaging</i> , 2001, 4, 181-184.	0.1	1
429	Reversible Interconnection Using Thin Films of Hydrogen Storage Alloys.. <i>Journal of Japan Institute of Electronics Packaging</i> , 2001, 4, 142-144.	0.1	0
430	Lead-free soldering - future aspects of toxicity, energy and resource consumption. , 2001, , .		6
431	<title>MEMS IC test probe utilizing fritting contacts</title>. , 2000, 4019, 244.		4
432	Morphology and microstructure of the Ar ⁺ -ion sputtered (0001) α -Al ₂ O ₃ surface. <i>Applied Surface Science</i> , 2000, 165, 159-165.	6.1	20

#	ARTICLE	IF	CITATIONS
433	Influence of Substrate Surface Shape on Peel-off Strength between Aluminum Nitride Substrates and an Epoxy Modified Polyimide Adhesive.. Journal of Japan Institute of Electronics Packaging, 2000, 3, 494-500.	0.1	2
434	Effect of Heat Treatment and Residual Stress due to Contact Deformation on Fracture Behavior of Al/Sapphire Joint Fabricated by SAB. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 2000, 64, 691-697.	0.4	0
435	Tensile Properties and Analysis of Growth of Interfacial Defects by Finite Element Method in Al/Sapphire Joint Fabricated by SAB Process. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 2000, 64, 684-690.	0.4	1
436	Fracture Mechanical Approach to the Growth of Interfacial Defects in Al/Sapphire Joint Fabricated by SAB: Tearing-Off Test and Analysis by Finite Element Method. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 2000, 64, 444-450.	0.4	1
437	Characteristics of fritting contacts utilized for micromachined wafer probe cards. Review of Scientific Instruments, 2000, 71, 2224-2227.	1.3	18
438	Novel multibrige-structured piezoelectric microdevice for scanning force microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 3604.	1.6	43
439	1 à°ä½“é–“â†ç€ç¾4è±jã•ã,%ooã,æ,©æŽ¥â•æŠ€èj“ã; æŽ¥â•ã¼•ã° ãã®èj“éçç²—ã•ã®ã½±éÿ¿. Yosetsu Gakkai Shi/Journal of the Japan Institute of Electronics Packaging, 2000, 3, 621-626.	0.1	3
440	A New Ara of System Integration and Packaging. Journal of Japan Institute of Electronics Packaging, 2000, 3, 621-626.	0.1	3
441	Roadmap for Commercialization of Lead-Free Solder. Journal of Japan Institute of Electronics Packaging, 2000, 3, 422-425.	0.1	0
442	Union of Ecodesigners. Journal of Japan Institute of Electronics Packaging, 2000, 3, 376-377.	0.1	0
443	Si/Si Interface Bonded at Room Temperature by Ar Beam Surface Activation. Materials Science Forum, 1999, 294-296, 341-344.	0.3	4
444	Room-Temperature Bonding of Si Wafers to Pt Films on SiO2 or LiNbO3 Substrates Using Ar-Beam Surface Activation. Japanese Journal of Applied Physics, 1999, 38, L1559-L1561.	1.5	18
445	Microfabricated Dynamic Scanning Force Microscope Using a Three Dimensional Piezoelectric T-shape Actuator. Japanese Journal of Applied Physics, 1999, 38, 7180-7184.	1.5	13
446	Tip-Scanning Dynamic Force Microscope Using Piezoelectric Cantilever for Full Wafer Inspection. Japanese Journal of Applied Physics, 1999, 38, 7155-7158.	1.5	5
447	Transmission Electron Microscope Observations of Si/Si Interface Bonded at Room Temperature by Ar Beam Surface Activation. Japanese Journal of Applied Physics, 1999, 38, 1589-1594.	1.5	89
448	Room-temperature bonding of lithium niobate and silicon wafers by argon-beam surface activation. Applied Physics Letters, 1999, 74, 2387-2389.	3.3	91
449	Reversible interconnection by control of interface reactions. , 1999, , .		2
450	Reversible interconnection using hydrogen storage alloy. , 1999, , .		1

#	ARTICLE	IF	CITATIONS
451	Disassemblability assessment for IM. , 1999, , .		4
452	Self-excited piezoelectric PZT microcantilevers for dynamic SFM with inherent sensing and actuating capabilities. Sensors and Actuators A: Physical, 1999, 72, 179-188.	4.1	122
453	Atomic structure of Al/Al interface formed by surface activated bonding. Journal of Materials Science, 1999, 34, 4133-4139.	3.7	46
454	Active disassembly of bonded wafers. , 1999, , .		4
455	Environmentally Conscious Engineering-EcoDesign. Eco-Design and Sustainable Development.. Journal of Japan Institute of Electronics Packaging, 1999, 2, 571-575.	0.1	0
456	Relation between Plasticity of Al and Bonded Area Fraction in Al/Sapphire Joint Fabricated by SAB. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 1999, 63, 1485-1489.	0.4	0
457	Effect of the surface treatment on the room-temperature bonding of Al to Si and SiO ₂ . Journal of Materials Science, 1998, 33, 253-258.	3.7	22
458	Low-temperature direct bonding of silicon and silicon dioxide by the surface activation method. Sensors and Actuators A: Physical, 1998, 70, 164-170.	4.1	91
459	Microstructure of Al/Al ₂ O ₃ Interface Fabricated by Surface Activated Bonding at Room Temperature. Materials Science Forum, 1998, 294-296, 329-332.	0.3	1
460	Effect of Surface Roughness on Room-Temperature Wafer Bonding by Ar Beam Surface Activation. Japanese Journal of Applied Physics, 1998, 37, 4197-4203.	1.5	169
461	1.3 μm InGaAsP/InP lasers on GaAs substrate fabricated by the surface activated wafer bonding method at room temperature. Applied Physics Letters, 1998, 72, 1565-1566.	3.3	53
462	InGaAsP Lasers on GaAs Fabricated by the Surface Activated Wafer Direct Bonding Method at Room Temperature. Japanese Journal of Applied Physics, 1998, 37, 1405-1407.	1.5	10
463	Design Concept of the Latest System Packaging. Electronic System Integration-An Interim Report from the Advisory Committee of MITI.. Journal of Japan Institute of Electronics Packaging, 1998, 1, 104-107.	0.1	0
464	Frequency modulation detection high vacuum scanning force microscope with a self-oscillating piezoelectric cantilever. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1647.	1.6	9
465	Novel high vacuum scanning force microscope using a piezoelectric cantilever and the phase detection method. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1551.	1.6	20
466	Development of a piezoelectric self-excitation and self-detection mechanism in PZT microcantilevers for dynamic scanning force microscopy in liquid. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1559.	1.6	53
467	Characterization of micromachined piezoelectric PZT force sensors for dynamic scanning force microscopy. Review of Scientific Instruments, 1997, 68, 2091-2100.	1.3	73
468	Microstructure and strength of Al-sapphire interface by means of the surface activated bonding method. Journal of Materials Research, 1997, 12, 852-856.	2.6	15

#	ARTICLE	IF	CITATIONS
469	Pressureless Silicon Direct Bonding at Room Temperature by Argon Beam Etching. IEEJ Transactions on Sensors and Micromachines, 1997, 117, 420-425.	0.1	1
470	Room temperature GaAs π -Si and InP π -Si wafer direct bonding by the surface activated bonding method. Nuclear Instruments & Methods in Physics Research B, 1997, 121, 203-206.	1.4	54
471	Materials science communication mechanism of the anodic bonding between pzt ceramics and silicon wafer. Materials Chemistry and Physics, 1997, 51, 174-177.	4.0	12
472	Title is missing!. Journal of Materials Science, 1997, 5, 279-286.	1.2	12
473	Wafer direct bonding of compound semiconductors and silicon at room temperature by the surface activated bonding method. Applied Surface Science, 1997, 117-118, 808-812.	6.1	71
474	Sol-gel derived PNNZT thin films for micromachined piezoelectric force sensors. Thin Solid Films, 1997, 299, 88-93.	1.8	7
475	Micromachined piezoelectric force sensors based on PZT thin films. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 1996, 43, 553-559.	3.0	77
476	Preparation and Properties of Piezoelectric Lead Zirconate Titanate Thin Films for Microsensors and Microactuators by Sol-Gel Processing. Journal of the Ceramic Society of Japan, 1996, 104, 159-163.	1.3	46
477	Deflection detection and feedback actuation using a self-excited piezoelectric Pb(Zr,Ti)O ₃ microcantilever for dynamic scanning force microscopy. Applied Physics Letters, 1996, 69, 2036-2038.	3.3	78
478	Sol-gel derived PZT force sensor for scanning force microscopy. Materials Chemistry and Physics, 1996, 44, 25-29.	4.0	30
479	Self-excited force-sensing microcantilevers with piezoelectric thin films for dynamic scanning force microscopy. Sensors and Actuators A: Physical, 1996, 54, 477-481.	4.1	42
480	Surface activated bonding of silicon wafers at room temperature. Applied Physics Letters, 1996, 68, 2222-2224.	3.3	397
481	Fabrication of 10-Nanometer-scale GaAs Dot Structures by In Situ Selective Gas Etching with Self-Assembled InAs Dots as a Mask. Japanese Journal of Applied Physics, 1995, 34, L1198-L1201.	1.5	6
482	Title is missing!. Journal of Micromechanics and Microengineering, 1995, 5, 231-236.	2.6	16
483	Piezoelectric Sensor for Detecting Force Gradients in Atomic Force Microscopy. Japanese Journal of Applied Physics, 1994, 33, 334-340.	1.5	32
484	Piezoelectric force sensor for scanning force microscopy. Sensors and Actuators A: Physical, 1994, 43, 305-310.	4.1	24
485	Determination of residual stresses in bimetals. Journal of Materials Science, 1994, 29, 1441-1448.	3.7	8
486	Force sensing microcantilever using sputtered zinc oxide thin film. Applied Physics Letters, 1994, 64, 37-39.	3.3	56

#	ARTICLE	IF	CITATIONS
487	Electronic Process of Joining Metal and Ceramic by "Surface Activated Bonding"; Materials Research Society Symposia Proceedings, 1994, 337, 727.	0.1	0
488	Microstructure of B ₄ C/TiB ₂ Composite Fabricated by Reaction Sintering of B ₄ C and TiC. Journal of the Ceramic Society of Japan, 1994, 102, 321-325.	1.3	11
489	Development of a force sensor for atomic force microscopy using piezoelectric thin films. Nanotechnology, 1993, 4, 218-224.	2.6	113
490	Special Issue on Nanometer-scale Machining and Processing Technology - From the Viewpoint of Chemical/Physical Reaction on Surfaces. Nanometer-scale Assembly Technology.. Journal of the Japan Society for Precision Engineering, 1993, 59, 572-576.	0.1	0
491	Structure of AlAl and AlSi ₃ N ₄ interfaces bonded at room temperature by means of the surface activation method. Acta Metallurgica Et Materialia, 1992, 40, S133-S137.	1.8	194
492	Designing structural defects to relieve thermal stress. Acta Metallurgica Et Materialia, 1992, 40, S289-S293.	1.8	7
493	Mechanochemical Polishing of Silicon Carbide Single Crystal with Chromium(III) Oxide Abrasive. Journal of the American Ceramic Society, 1992, 75, 189-194.	3.8	76
494	Development of a New Mechanochemical Polishing Method with a Polishing Film for Ceramic Round Bars. CIRP Annals - Manufacturing Technology, 1992, 41, 339-342.	3.6	15
495	The Feasibility of Room Temperature Joining.. Yosetsu Gakkai Shi/Journal of the Japan Welding Society, 1992, 61, 98-106.	0.1	1
496	Low Resistivity Junction between YBa ₂ Cu ₃ O _{7-x} /i>&/sub>; Superconductor and Metals by Evaporation Method. Journal of the Ceramic Society of Japan, 1991, 99, 427-430.	1.3	1
497	Transmission Electron Microscopy of Surface Damages Resulting from Wet Polishing in a Polycrystalline Aluminum Nitride Substrate. Journal of the Ceramic Society of Japan, 1991, 99, 613-619.	1.3	4
498	CHEMICAL RELIEF OF THERMAL STRESS AT METAL/CERAMIC JOINED INTERFACE. Analytical Sciences, 1991, 7, 1231-1234.	1.6	2
499	A molecular-dynamic approach to interface crack problem.. Nihon Kikai Gakkai Ronbunshu, A Hen/Transactions of the Japan Society of Mechanical Engineers, Part A, 1991, 57, 678-685.	0.2	3
500	Low-Resistivity Contact of YBa ₂ Cu ₃ O _{7-x} /Al Joint Bonded at Room Temperature. Japanese Journal of Applied Physics, 1991, 30, L2028-L2031.	1.5	0
501	Environmental Effects on Structural, Mechanical and Electrical Properties of Al/Al Interfaces Joined at Room Temperature. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 1991, 55, 1002-1010.	0.4	9
502	A Computer-Aided Method for the Analysis of Crystal Orientations from Transmission Electron Diffraction Patterns Obtained Using a Single-Tilting Stage. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 1991, 55, 605-606.	0.4	0
503	High Resolution Electron Microscopy of Al/Si and Al/Si ₃ N ₄ Interfaces Prepared by Room Temperature Bonding Method. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 1991, 55, 907-908.	0.4	0
504	Resistivity of Sintered YBa ₂ Cu ₃ O _{7-x} at Large Current Density. Journal of the Ceramic Society of Japan, 1990, 98, 1361-1364.	1.3	1

#	ARTICLE	IF	CITATIONS
505	TEM Observation of the Al and Cu Interfaces Bonded at Room Temperature by Means of the Surface Activation Method. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 1990, 54, 713-719.	0.4	12
506	Transmission Electron Microscopy of Bi(Pb)-Sr-Ca-Cu-O Superconductor Prepared by the Intermediate Pressing Process. Japanese Journal of Applied Physics, 1990, 29, L2006-L2009.	1.5	12
507	Structural features to relax thermal stress at metal/ceramic joined interface.. ISIJ International, 1990, 30, 1041-1045.	1.4	8
508	Functional processing for materials. Materials interconnection.. Journal of the Japan Society for Precision Engineering, 1990, 56, 989-994.	0.1	1
509	TEM Observation of Al/Al Interface Prepared in an Ultrahigh Vacuum at Room Temperature. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 1990, 54, 741-742.	0.4	0
510	Mechanochemical polishing of sintered silicon nitride.. Journal of the Japan Society for Precision Engineering, 1989, 55, 2247-2253.	0.1	4
511	Solid State Bonding of Si3N4 and Ni. Materials Research Society Symposia Proceedings, 1989, 170, 99.	0.1	0
512	High Resolution Electron Microscopy of Alumina/Niobium Joined Interface and Analysis of the Joining Process. Nippon Kinzoku Gakkaishi/Journal of the Japan Institute of Metals, 1989, 53, 429-438.	0.4	2
513	Composite Parameters and Mechanical Compatibility of Material Joints. Journal of Composite Materials, 1988, 22, 917-934.	2.4	114
514	An analysis of weak-beam $\hat{\pm}$ Fringes formed by systematic diffractions. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1988, 58, 825-832.	0.6	5
515	Bond strength of vacuum brazed Mg-PSZ/steel joints. Materials Research Bulletin, 1987, 22, 1187-1193.	5.2	3
516	Haftfestigkeitsbestimmung an Keramik-Metall-Verbindungen mit Hilfe von Schichtverbundbiegeproben - Teil 1. Materialwissenschaft Und Werkstofftechnik, 1985, 16, 75-80.	0.9	16
517	Haftfestigkeitsbestimmung an Keramik-Metall-Verbindungen mit Hilfe von Schichtverbundbiegeproben - Teil 2. Materialwissenschaft Und Werkstofftechnik, 1985, 16, 122-128.	0.9	4
518	Fracture energy measurements of Ceramic Thermal Barrier Coatings. Materialwissenschaft Und Werkstofftechnik, 1984, 15, 371-377.	0.9	8
519	Room-temperature interconnection of electroplated Au microbump by means of surface activated bonding method. , 0, , .		12
520	Bump-less interconnect for next generation system packaging. , 0, , .		20
521	A new wafer-bonder of ultra-high precision using surface activated bonding (SAB) concept. , 0, , .		10
522	Bonding of p-Si/n-InP wafers through surface activated bonding method at room temperature. , 0, , .		3

#	ARTICLE	IF	CITATIONS
523	Low temperature direct Cu-Cu bonding with low energy ion activation method. , 0, , .		2
524	Low contact-force and compliant MEMS probe card utilizing fritting contact. , 0, , .		21
525	A lamination technique of LCP/Cu for electronic packaging. , 0, , .		10
526	Panel-size component integration (PCI) with molded liquid crystal polymer (LCP) substrates. , 0, , .		7
527	Reliability and microstructure of Au-Al and Au-Cu direct bonding fabricated by the Surface Activated Bonding. , 0, , .		7
528	Surface activated bonding for new flip chip and bumpless interconnect systems. , 0, , .		28
529	An integrated fabrication of sol-gel derived PZT thick films and SOI for 2D optical micromirror. , 0, , .		0
530	Room temperature vacuum sealing using surface activated bonding method. , 0, , .		18
531	Design and fabrication of an electrostatically actuated MEMS probe card. , 0, , .		7
532	Wideband and high reliability RF-MEMS switches using PZT/HfO/sub 2/ multi-layered high K dielectrics. , 0, , .		3
533	Surface Activated Bonding – High Density Packaging Solution for Advanced Microelectronic System. , 0, , .		4
534	A Novel Approach to Disassembly of Joined Interface. , 0, , .		4
535	Cu/LCP Laminated Materials for New Generation FPC. , 0, , .		0
536	Surface activation process of lead-free solder bumps for low temperature bonding. , 0, , .		4
537	Micro phenomena in low contact-force probing on aluminum. , 0, , .		0
538	Customization of The Toxic Potential Indicator for Japanese Regulation. , 0, , .		2
539	Room temperature vacuum sealing using surfaced activated bonding with au thin films. , 0, , .		9
540	Behavior of Surface Oxide and Intermetallic Compounds in Interconnections of Micro Sn-Ag Solder Bumps. , 0, , .		2

#	ARTICLE	IF	CITATIONS
541	A Novel Method for Bonding of Ionic Wafers. , 0, , .		1
542	Bumpless Interconnect of Cu Electrodes in Millions-Pins Level. , 0, , .		4
543	Room-Temperature Bonding of Vertical-Cavity Surface-Emitting Laser Chips on Si Substrates Using Au Microbumps in Ambient Air. Applied Physics Express, 0, 1, 112201.	2.4	76
544	Transfer Technology of Ferroelectric Films onto the Polymer Substrate for the Application of High Density Capacitor. Advanced Materials Research, 0, 74, 311-314.	0.3	0
545	Modified Diffusion Bonding of Chemical Mechanical Polishing Cu at 150 Å°C at Ambient Pressure. Applied Physics Express, 0, 2, 056501.	2.4	22
546	Foresight of eco-design in Chinese electric equipment manufacturing. , 0, , .		0